

a N-channel MOS transistor having:

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canceled  
a source-drain path which is coupled between the second output node and a predetermined potential which is lower than the first voltage; and

a gate electrode coupled to the selection node to which the signal selecting its corresponding word line may be supplied to open said [course-] source-drain path of the N-channel MOS transistor.

#### REMARKS

Claims 27 and 28 have been canceled. Claims 35, 37, 41, 42, 50, 51, 66, 68 and 73 have been amended to overcome the Examiner's rejection under 35 U.S.C. § 112. The claims as amended are now definite and find support in the specification.

Applicants respectfully traverse the rejections under 35 U.S.C. §103 of claims 21-28 and 34-76 over Takemae, Gupta, Asano and Watanabe for the following reasons:

In the Office Action, the Examiner repeats the same comments set forth in the previous action, stating "These claims apparently specify the broad and old concept of using word-line boost in a memory array". This leads Applicants to conclude that the Examiner does not appreciate how the claimed invention differs from a word-line drive system with a boost capacitor which is truly an old concept. Applicants agree with the Examiner that a mere application of high (boosted) voltage to word lines in a DRAM was well known prior to the filing of this application (before the priority date).

This prior art arrangement is not what the present invention is directed to. The present invention rather is directed to quickly supplying a boosted voltage to a word line, in order to achieve fast data reading in a DRAM. In this regard, this invention differs from the cited prior art. More specifically, the present invention includes a voltage generator circuit which generates a first voltage higher than a power supply voltage both when one of a plurality of words lines is selected and when none of the plurality of word lines is selected. When one of the plurality of word lines is selected, a word-line driver circuit corresponding to the selected

word line switches to apply the first voltage to the selected word line to thereby achieve fast drive of the word line. The structural elements therefore are defined in the claims and clearly differentiate the present invention from the cited art.

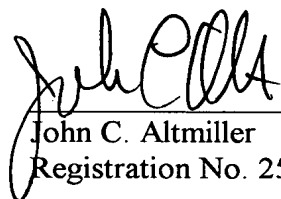
Applicants and the undersigned attorney would like to have an interview with the Examiner to discuss any remaining issues in this application. Applicant's attorney will be contacting the Examiner. Further, the Examiner is invited to call the undersigned at (202) 429-1776 to discuss any information concerning this application.

Applicants respectfully request a two month Extension of Time to respond to the Office Action of October 1, 1997. The extended period expires March 1, 1998.

The Office is hereby authorized to charge the fee of \$400.00 for a Petition for Extension of Time Under 37 C.F.R. § 1.136(a) and any additional fees under 37 C.F.R. § 1.16 or § 1.17 or credit any overpayment to Deposit Account No. 11-0600.

Respectfully submitted,

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